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1 ? On-Resistance Diamond Vertical-Schottky Barrier Diode Operated at 250 °C

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#	Paper	IF	Citations
87	High temperature operation of diamond power SBD. 2013 ,		1
86	High-Temperature Operation of Diamond Junction Field-Effect Transistors With Lateral p-n Junctions. <i>IEEE Electron Device Letters</i> , 2013 , 34, 1175-1177	4.4	42
85	High-temperature characteristics and stability of Cu/diamond Schottky diodes. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 04EP05	1.4	15
84	Diamond Metal Semiconductor Field-Effect Transistor With Breakdown Voltage Over 1.5 kV. <i>IEEE Electron Device Letters</i> , 2014 , 35, 1112-1114	4.4	95
83	Thermal stabilization and deterioration of the WC/p-type diamond (100) Schottky-barrier interface. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014 , 211, 2363-2366	1.6	10
82	Leakage current analysis of diamond Schottky barrier diodes operated at high temperature. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 04EP04	1.4	9
81	Zr/oxidized diamond interface for high power Schottky diodes. <i>Applied Physics Letters</i> , 2014 , 104, 052105	5.4	91
80	Anisotropic lateral growth of homoepitaxial diamond (111) films by plasma-enhanced chemical vapor deposition. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 04EH04	1.4	17
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74	600 V Diamond Junction Field-Effect Transistors Operated at 200°C. <i>IEEE Electron Device Letters</i> , 2014 , 35, 241-243	4.4	60
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69	Fabrication and characterization of a corner architecture Schottky barrier diode structure. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015 , 212, 2410-2417	1.6	7
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